

| L Numb r | Hits | S ar h Text | DB | Time stamp |
|----------------|------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------|---------------------|
| 165 | 2710 | substrate same (insulating or dielectric) and (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction | USPAT; US-PGPUB; EPO; JP ; DERWENT; IBM_TDB | 2004/06/10 12:02 |
| 166 | 849 | substrate same (insulating or dielectric) and (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:02 |
| 167 | 707 | substrate same (insulating or dielectric) and (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:02 |
| 168 | 41 | (substrate same (insulating or dielectric) and (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:03 |
| 169 | 35 | (substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:03 |
| 170 | 32 | (substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:04 |
| 171 | 13 | (substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:05 |
| 172 | 13 | (substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) sam (third or fourth)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:05 |

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| 173 | 9 | (substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:06 |
| 174 | 8 | (substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same electrode same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:06 |
| 175 | 2 | (substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same (control adj electrode) same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:08 |
| 176 | 2 | ((substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same (control adj electrode) same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm.) and (concentration near2 higher).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:09 |
| 177 | 2 | ((substrate same (insulating or dielectric) same (type or conductivity) same (impurity or concentration) same (higher or lower) same (control adj electrode) same junction same (film or layer) same (first or second or third or fourth or upper or lower or top or bottom) same (third or fourth)) and (control near electrode).clm.) and (conductivity).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:09 |
| 178 | 0 | (control adj electrode) and (first near conductivity near type) and (second near conductivity near type) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:11 |
| 179 | 0 | (control adj electrode) and (first near conductivity near type) and (second near conductivity near type) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:11 |

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| 180 | 1333 | (control adj electrode) and (first near conductivity near type) and (second near conductivity near type) | USPAT; US-PGPUB; EP ; JPO; DERWENT; IBM_TDB | 2004/06/10 12:11 |
| 181 | 137 | (control adj electrode) and (first near conductivity near type) and (second near conductivity near type) and ((third or fourth) near2 layer) and ((insulation or insulator or dielectric) near2 (layer or film)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:12 |
| 182 | 58 | (control adj electrode) and (first near conductivity near type) and (second near conductivity near type) and ((third or fourth) near2 layer) and ((insulation or insulator or dielectric) near2 (layer or film)) and ((first or second or third or fourth) near2 concentration) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:13 |
| 183 | 27 | (control adj electrode).clm. and ((first or second or third) near conductivity).clm. and ((third or fourth) near2 layer) and ((insulation or insulator or dielectric) near2 (layer or film)) and ((first or second or third or fourth) near2 concentration).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:15 |
| 184 | 96 | (control adj electrode).clm. and ((first or second or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:23 |
| 185 | 53 | (control adj electrode).clm. and ((first or second or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. and ((third or fourth) near2 layer).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:19 |
| 186 | 26 | (control adj electrode).clm. and ((first or second or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. and junction.clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:34 |
| 187 | 11 | (control adj electrode).clm. and ((first or second or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. and (junction same (control adj electrode)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:35 |

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| 188 | 7 | (contr l adj le trode).clm. and ((first or s ond or third) near conductivity).clm. and ((in ulati n r insulat r r di lectric r insulating) near2 (lay r r film)). lm. and ((first r second r third r fourth) near2 conc ntration). lm. and (junction near10 (control adj electrode)).clm. | USPAT; US-PGPUB; EP ; JPO; DERWENT; IBM_TDB | 2004/06/10 12:37 |
| 189 | 6 | (control adj electrode).clm. and ((first or scond or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. and (junction near10 (control adj electrode)).clm. and (concentration near3 (higher or lower)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:37 |
| 190 | 6 | (control adj electrode).clm. and ((first or scond or third) near conductivity).clm. and ((insulation or insulator or dielectric or insulating) near2 (layer or film)).clm. and ((first or second or third or fourth) near2 concentration).clm. and (junction near10 (control adj electrode)).clm. and (concentration near2 (higher or lower)).clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:38 |
| 191 | 97 | (first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region or layer or portion)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:39 |
| 192 | 63 | (first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:41 |
| 193 | 6 | (first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction near5 conductivity) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:42 |
| 194 | 15 | (first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction near10 conductivity) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:42 |
| 195 | 0 | (first near conductivity near type) and (second n ar conductivity near typ) and (f urth n ar2 (regi n)) and (ntral adj el trode) and juncti n and ((impurity adj concentrati n) n ar (high r r lower)) and (junction near10 c nductivity near10 (ontrol adj le tr d)) | USPAT; US-P PUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:43 |

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| 196 | 63 | (first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and junction | USPAT; US-PGPUB; EP ; JPO; DERWENT; IBM_TDB | 2004/06/10 12:43 |
| 197 | 29 | (first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and junction.ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:44 |
| 198 | 5 | (first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction same conductivity same (control adj electrode)).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:46 |
| 199 | 3 | (first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction same conductivity same (control adj electrode) same ((insulating or insulation or dielectric) near2 (layer or film))).ti,ab,clm. | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:47 |
| 200 | 0 | (first near conductivity near type) and (second near conductivity near type) and (fourth near2 (region)) and (control adj electrode) and junction and ((impurity adj concentration) near (higher or lower)) and (junction same conductivity same (control adj electrode) same ((insulating or insulation or dielectric) near2 (layer or film))).ti,ab,clm. and capacitance | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/06/10 12:47 |